



Dual N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}$ (Ω)	I _D (A) ^d	Q _g (Typ.)		
60	0.012 at V _{GS} = 10 V	38	23 nC		

FEATURES

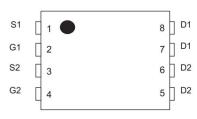
- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- AEC-Q101 Qualified for Automotive Applications



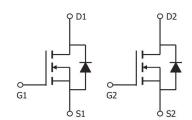
RoHS

APPLICATIONS

- 12 V Automotive systems
- · Motors, lamps and solenoid control
- Transmission control
- · Ultra high performance power switching



Top View



Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	60	V	
Gate-Source Voltage		V _{GS}	± 20	v
	T _C = 25 °C		38 ^a	
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 70 °C	1	32	
Continuous Diain Current (1) = 150 °C)	T _A = 25 °C	l _D	25 ^{b, c}	
	T _A = 70 °C	1 -	18 ^{b, c}	Α
Pulsed Drain Current		I _{DM}	164	A
Continuous Source Drain Diada Current	T _C = 25 °C	i	30	
Continuous Source-Drain Diode Current	T _A = 25 °C	- I _S -	25 ^{b, c}	
Avalanche Current	1 = 0.411	I _{AS}	31	
Single-Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	56	mJ
Maximum Power Dissipation	T _C = 25 °C		55	
	T _C = 70 °C		35	W
	T _A = 25 °C	P _D	35 ^{b, c}	VV
	T _A = 70 °C	1	23 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	55 to 175	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R _{thJA}	35	45	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	3	8		

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 10 s
- d. Maximum under Steady State conditions is 85 °C/W.



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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static		I .					
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V, } I_{D} = 250 \mu\text{A}$	60			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	1 050 1		55			
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA		- 6.3		mV/°C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = 48V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 48 V, V _{GS} = 0 V, T _J = 55 °C			10	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	38			Α	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 10A		0.012	0.017	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 10A		50		S	
Dynamic ^b							
Input Capacitance	C _{iss}			1850		pF	
Output Capacitance	C _{oss}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		255			
Reverse Transfer Capacitance	C _{rss}			103			
Total Gate Charge	Q_g			23		nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = 48 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 10 \text{ A}$		4.5			
Gate-Drain Charge	Q _{gd}			8.2			
Gate Resistance	R _g	f = 1 MHz		4.3	5.5	Ω	
Turn-On Delay Time	t _{d(on)}			12	15	ne	
Rise Time	t _r	$V_{DD} = 48 \text{ V}, R_{L} = 5.4 \Omega$		30	55		
Turn-Off DelayTime	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		20	30		
Fall Time	t _f			20	26		
Turn-On Delay Time	t _{d(on)}			8	15	ns	
Rise Time	t _r	$V_{DD} = 48 \text{ V}, R_{L} = 5.4 \Omega$		13	15		
Turn-Off DelayTime	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		15	20		
Fall Time	t _f			10	15		
Drain-Source Body Diode Characterist	ics						
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			38	A	
Pulse Diode Forward Current ^a	I _{SM}				164		
Body Diode Voltage	V _{SD}	I _S = 2 A		0.7	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			25	50	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	L = 5.5 A dl/dt = 100 A/vo T = 25.00		25	50	nC	
Reverse Recovery Fall Time	t _a	$I_F = 5.5 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		19		20	
verse Recovery Rise Time t _b			6		ns		

Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

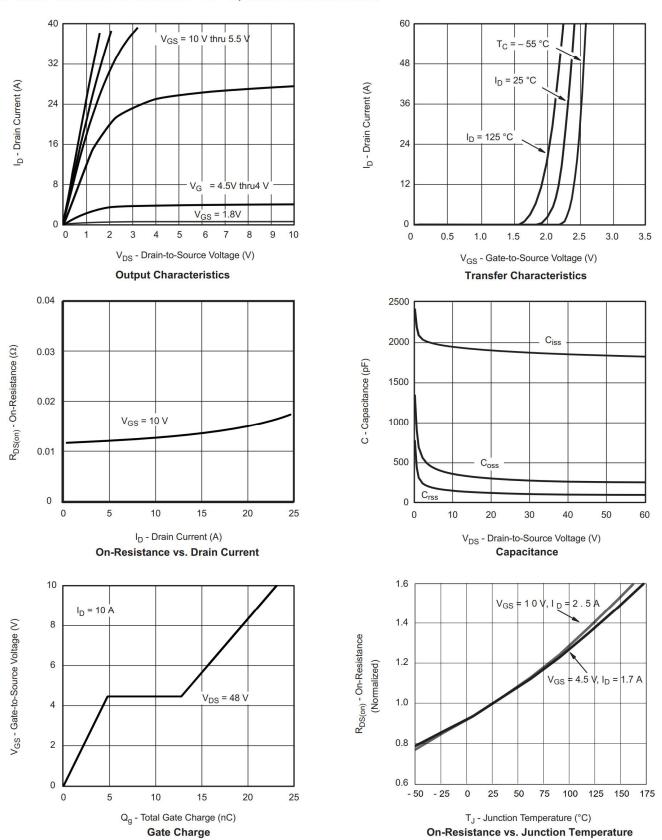
a. Pulse test; pulse width $\leq 300~\mu\text{s},$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.



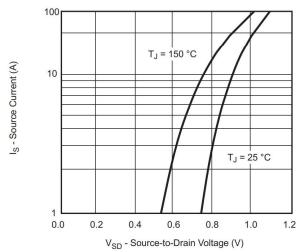


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

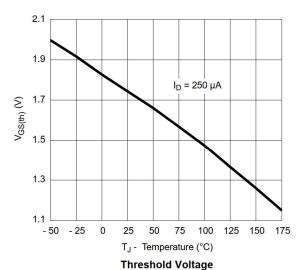




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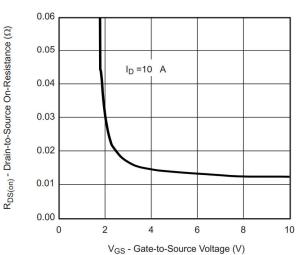


Source-Drain Diode Forward Voltage

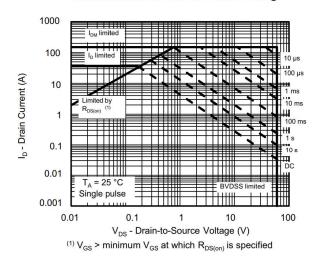


48
40
40
32
24
24
0
0
25
50
75
100
125
150
175
T_C - Case Temperature (°C)

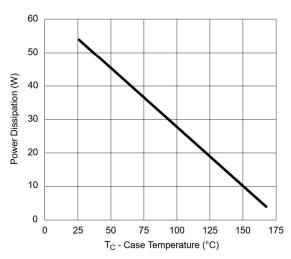
Current Derating*



On-Resistance vs. Gate-to-Source Voltage



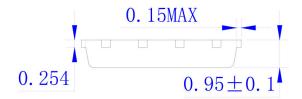
Safe Operating Area, Junction-to-Ambient

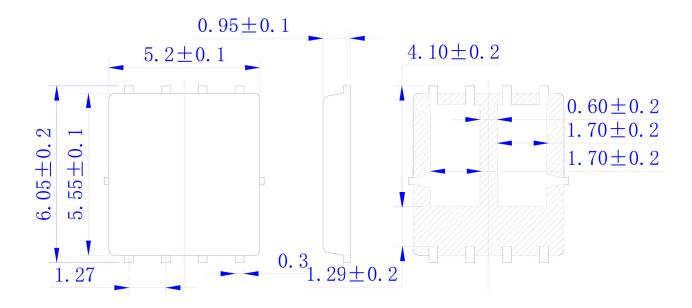


Power Derating

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DFN5×6 PACKAGE OUTLINE









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